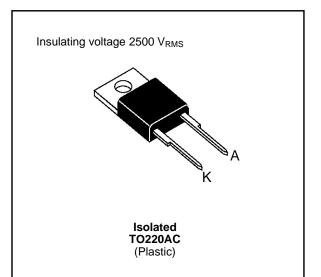


BYT 12PI-1000

FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- INSULATED: Capacitance 7pF



SUITABLE APPLICATIONS

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
Vrrm	Repetitive Peak Reverse Voltage		1000	V
V _{RSM}	Non Repetitive Peak Reverse Voltage		1000	V
I _{FRM}	Repetive Peak Forward Current	t _p ≤ 10μs	150	А
I _{F (RMS)}	RMS Forward Current		25	А
I _{F (AV)}	Average Forward Current	$\begin{array}{l} T_{c}=50^{\circ}C\\ \delta=0.5 \end{array}$	12	A
I _{FSM}	Surge non Repetitive Forward Current	t _p = 10ms Sinusoidal	75	A
Р	Power Dissipation	$T_c = 50^{\circ}C$	25	W
T _{stg} Tj	Storage and Junction Temperature Range		- 40 to + 150 - 40 to + 150	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th (j - c)}	Junction-case	4	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Synbol	Test Conditions			Тур.	Max.	Unit
I _R	T _j = 25°C	$V_R = V_{RRM}$			50	μA
	T _j = 100°C				2.5	mA
VF	T _j = 25°C	I _F = 12A			1.9	V
	T _j = 100°C				1.8	

RECOVERY CHARACTERISTICS

Symbol		Test Conditions					Max.	Unit
t _{rr}	T _j = 25°C	I _F = 1A	di _F /dt = - 15A/µs	$V_R = 30V$			155	ns
		I _F = 0.5A	I _R = 1A	$I_{rr} = 0.25A$			65	

TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol	Test Conditions			Тур.	Max.	Unit
t _{IRM}	di _F /dt = - 50A/µs	V _{CC} = 200 V I _F = 12A			200	ns
	diғ/dt = - 100A/µs	L _p ≤ 0.05μH T _j = 100°C See figure 11		120		
I _{RM}	di _F /dt = -50A/µs				7.8	А
	di⊧/dt = - 100A/µs			9		

TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol	Test Conditions				Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$,	c = 200V = 12μΗ	$I_F = I_F (AV)$ See figure 12			4.5	

To evaluate the conduction losses use the following equations:

 $V_F = 1.47 + 0.026 I_F \qquad \qquad P = 1.47 \ x \ IF_{(AV)} + 0.026 \ I_F^{2}_{(RMS)}$

Figure 1. Low frequency power losses versus average current

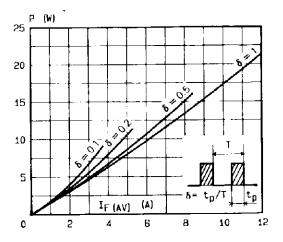


Figure 2. Peak current versus form factor

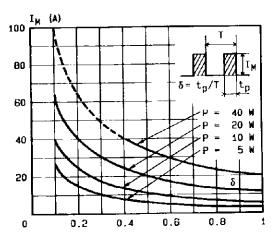




Figure 3. Non repetitive peak surge current versus overload duration

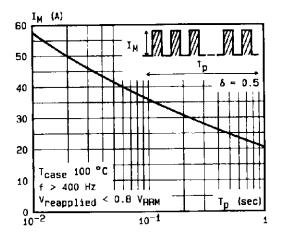


Figure 5. Voltage drop versus forward current

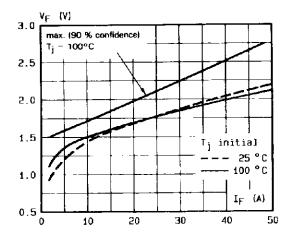


Figure 7. Recovery time versus di_F/dt-

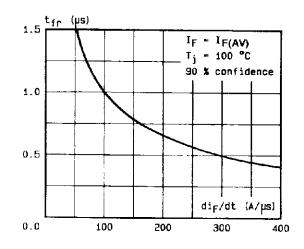


Figure 4. Thermal impedance versus pulse width

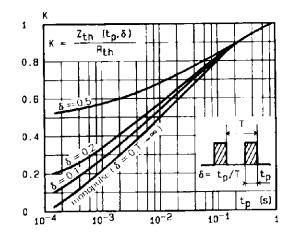


Figure 6. Recovery charge versus diF/dt-

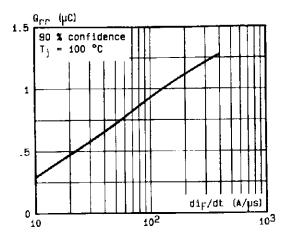
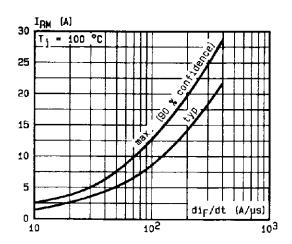


Figure 8. Peak reverse current versus diF/dt-





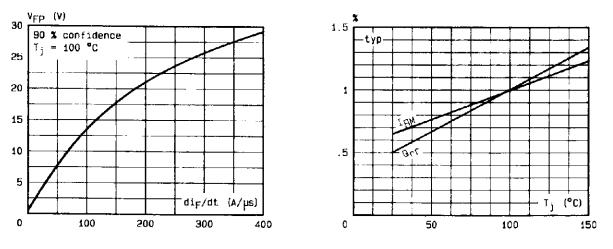


Figure 9. Peak forward voltage versus di_F/dt-

Figure 10. Dynamic parameters versus junction temperature.

Figure 11. Turn-off switching characteristics (without series inductance).

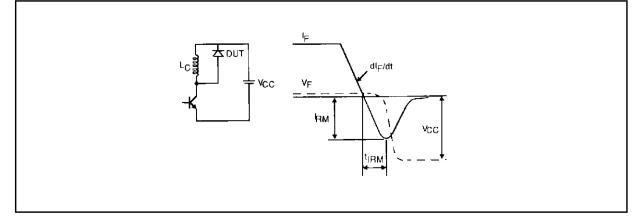
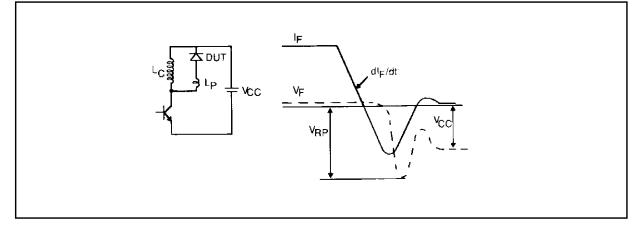


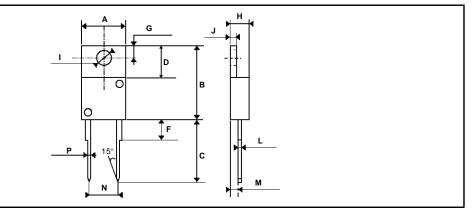
Figure 12. Turn-off switching characteristics (with series inductance)





PACKAGE MECHANICAL DATA :

Isolated TO220AC Plastic



	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
А	10.20	10.50	0.401	0.413		
В	14.23	15.87	0.560	0.625		
С	12.70	14.70	0.500	0.579		
D	5.85	6.85	0.230	0.270		
F		4.50		0.178		
G	2.54	3.00	0.100	0.119		
Н	4.48	4.82	0.176	0.190		
I	3.55	4.00	0.140	0.158		
J	1.15	1.39	0.045	0.055		
L	0.35	0.65	0.013	0.026		
М	2.10	2.70	0.082	0.107		
N	4.58	5.58	0.18	0.22		
Р	0.64	0.96	0.025	0.038		

Cooling method: by conduction (method C) Marking: type number Weight: 2.42g Recommended torque value: 80cm. N Maximum torque value: 100cm. N

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